

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

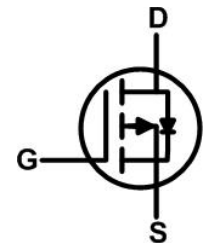
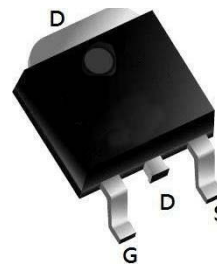
Product Summary


BVDSS	RDSON	ID
-150V	75mΩ	-30A

Description

The XR30P15H is the highest performance trench P-ch MOSFETs with extreme high cell density, which provides excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XR30P15H meets the RoHS and Green Product requirements, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-30	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-17.7	A
I_{DM}	Pulsed Drain Current ²	-112	A
EAS	Single Pulse Avalanche Energy ³	204.8	mJ
I_{AS}	Avalanche Current	-32	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	142	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.9	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-150	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-1A	---	75	95	mΩ
		V _{GS} =-4.5V, I _D =-1A	---	---	---	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-2.5	-3.0	-3.5	V
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-150V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-150V, V _{GS} =0V, T _J =100°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-3	---	55	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	5	---	Ω
Q _g	Total Gate Charge	V _{DS} =-75V, V _{GS} =-10V, I _D =-15A	---	137.5	---	nC
Q _{gs}	Gate-Source Charge		---	23	---	
Q _{gd}	Gate-Drain Charge		---	37.2	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =-10V, V _{DS} =-75V, I _D =-15A, R _{GEN} =3Ω	---	18.5	---	ns
T _r	Rise Time		---	80	---	
T _{d(off)}	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	72	---	
C _{iss}	Input Capacitance	V _{DS} =-75V, V _{GS} =0V, f=1MHz	---	6020	---	pF
C _{oss}	Output Capacitance		---	125	---	
C _{rss}	Reverse Transfer Capacitance		---	112	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-30	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-3A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-3A, di/dt=100A / μs,	---	---	---	nS
Q _{rr}	Reverse Recovery Charge	T _J = 25 °C	---	---	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C
2. The EAS data shows Max. rating . The test condition is VDD=-25V, VG=-10V, RG=25ohm, L=0.4mH
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical And Thermal Characteristics (Curves)

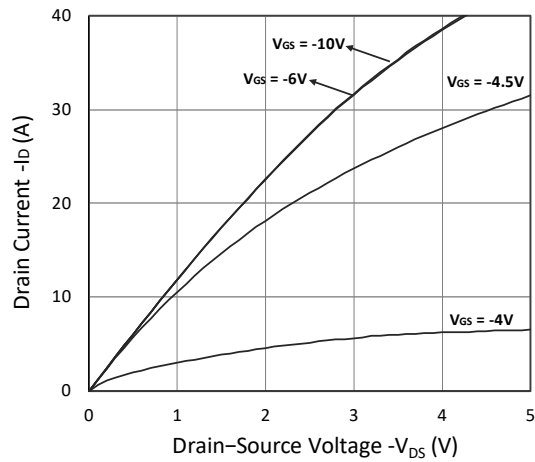


Figure 1. Output Characteristics

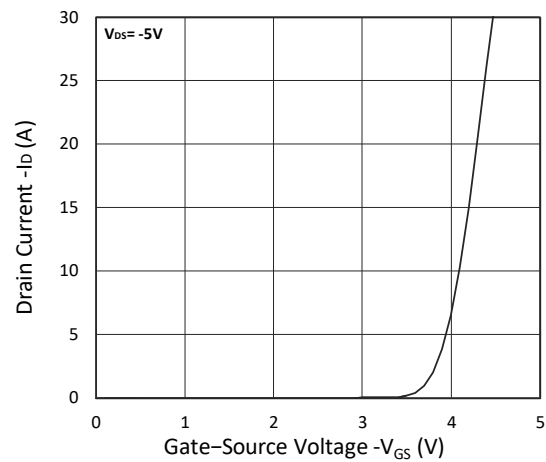


Figure 2. Transfer Characteristics

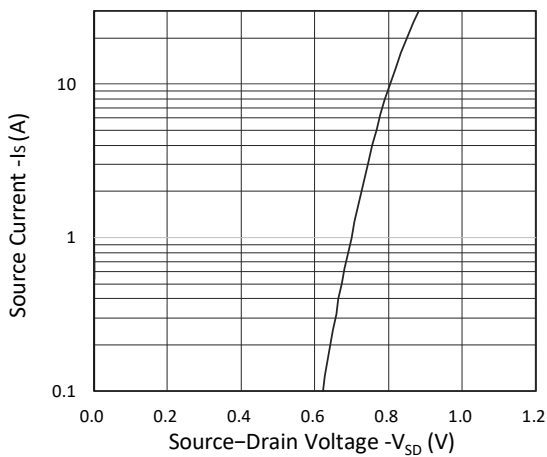


Figure 3. Forward Characteristics of Reverse

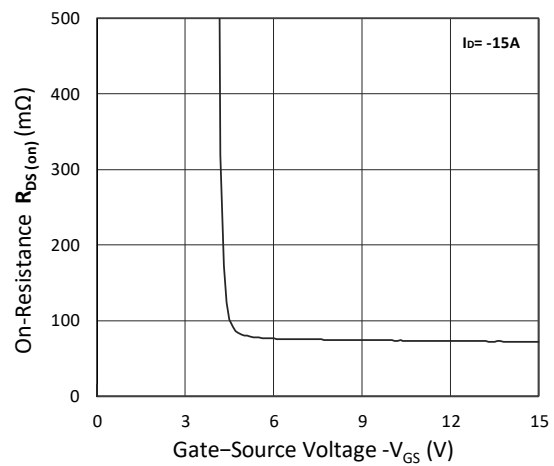


Figure 4. $R_{DS(on)}$ vs. V_{GS}

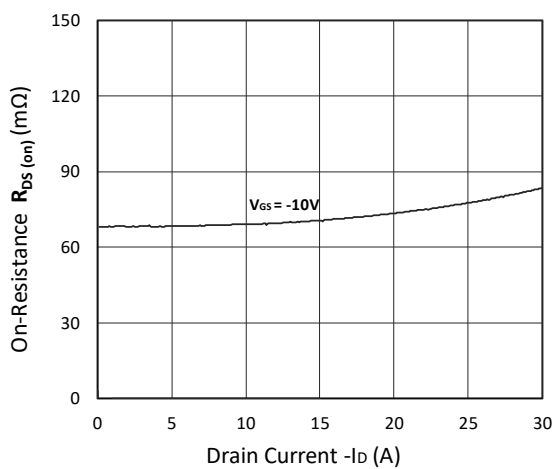


Figure 5. $R_{DS(on)}$ vs. I_D

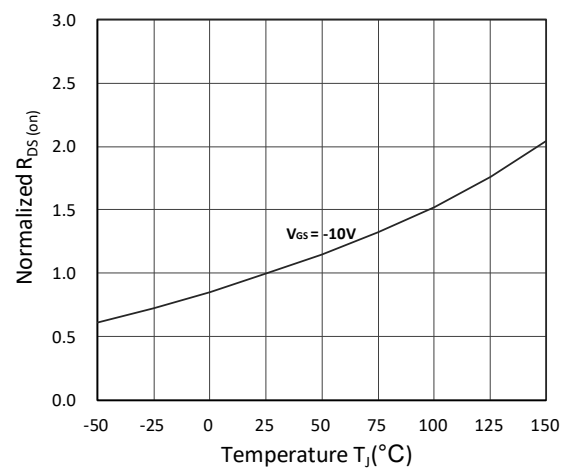


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

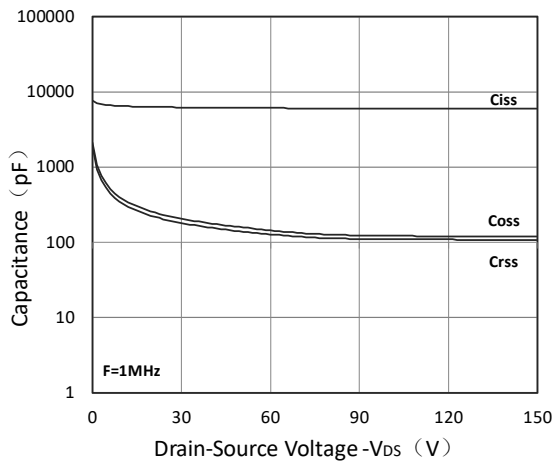


Figure 7. Capacitance Characteristics

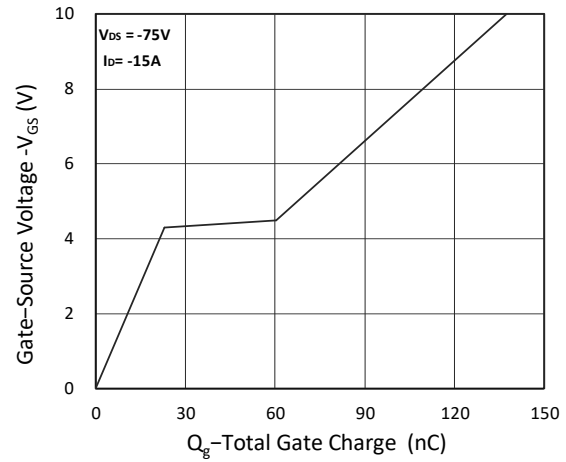


Figure 8. Gate Charge Characteristics

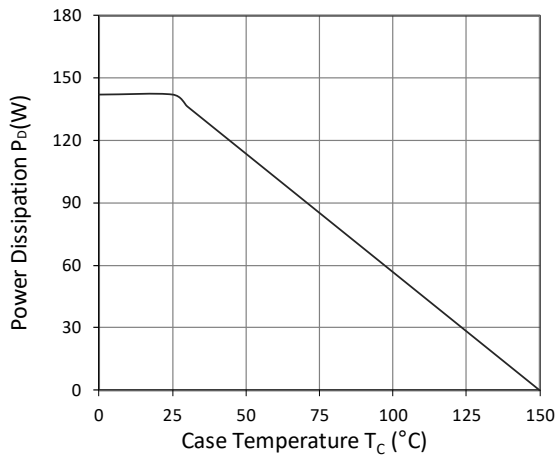


Figure 9. Power Dissipation

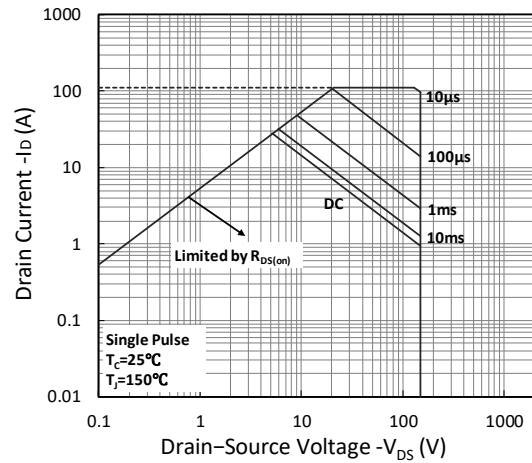


Figure 10. Safe Operating Area

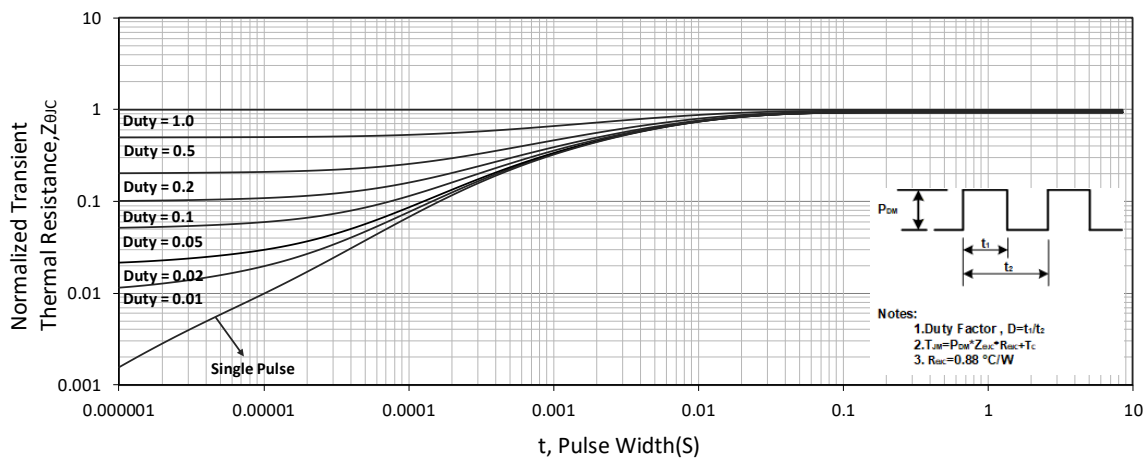
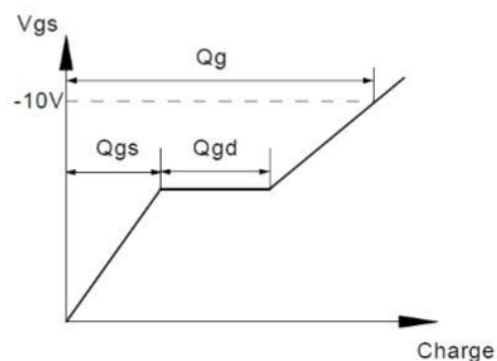
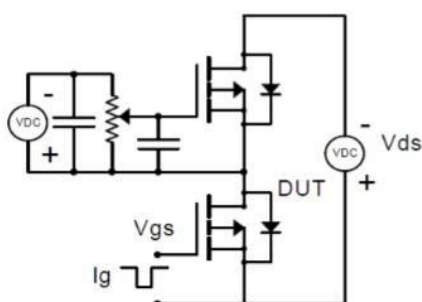


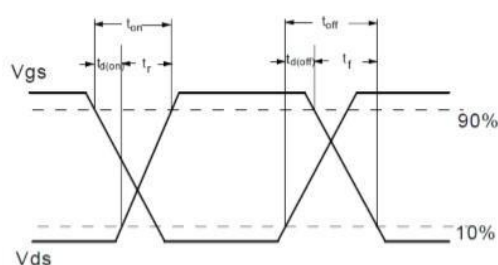
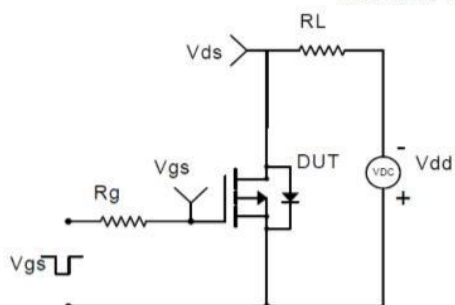
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

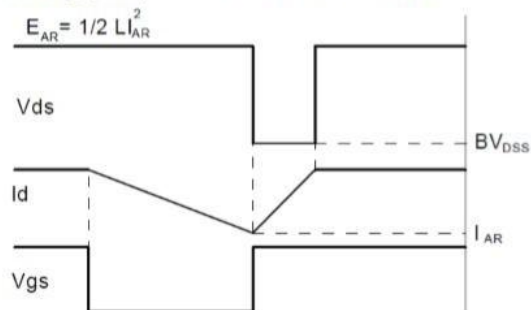
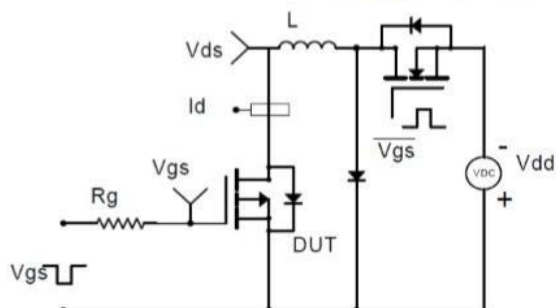
Gate Charge Test Circuit & Waveform



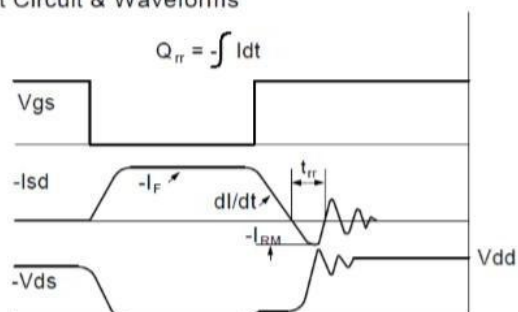
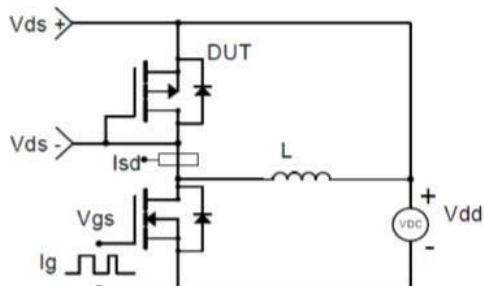
Resistive Switching Test Circuit & Waveforms



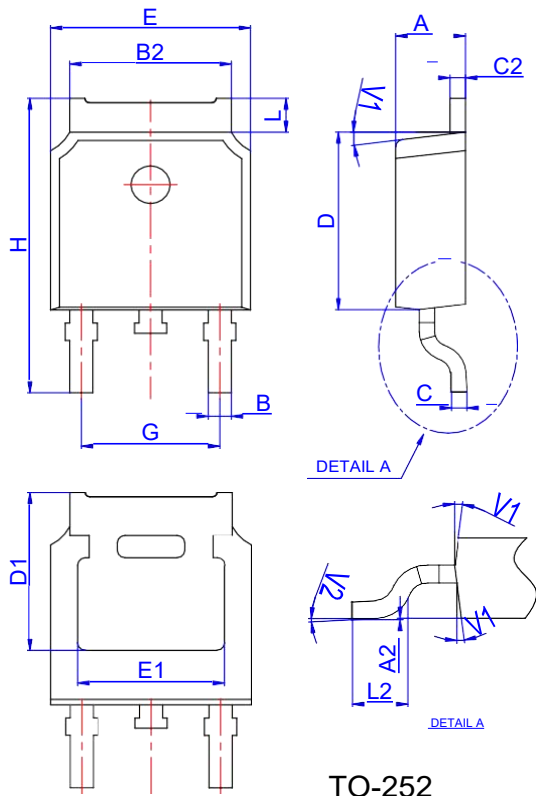
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



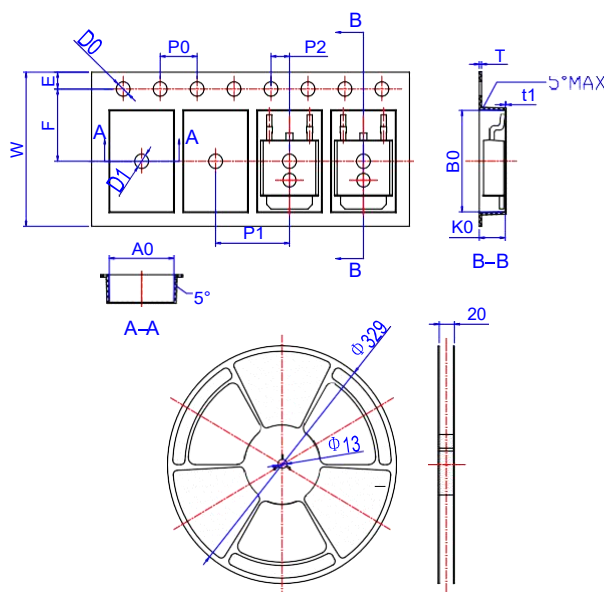
Package Mechanical Data-TO-252



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583